

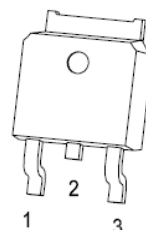


TO-252-2L Plastic-Encapsulate MOSFETS

CJU10N10 N-Channel Power MOSFET

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
100V	$0.14\Omega@10V$	9.6A

TO-252-2L



1. GATE
2. DRAIN
3. SOURCE

GENERAL DESCRIPTION

The CJU10N10 provide excellent $R_{DS(ON)}$, low gate charge and operation with low gate voltages. This device is suitable for use as a load switch or in PWM applications.

FEATURE

- Excellent package for good heat dissipation
- Ultra low gate charge
- Low reverse transfer capacitance
- Fast switching capability
- Avalanche energy specified

APPLICATION

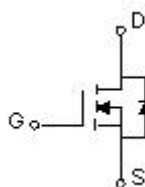
- Power switching application

MARKING



CJU10N10= Device code
Solid dot = Green molding compound device,
if none, the normal device
XXX=Date Code

EQUIVALENT CIRCUIT



Maximum ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	9.6	A
Pulsed Drain Current	I_{DM}	38.4	
Single Pulsed Avalanche Energy (note1)	E_{AS}	150	mJ
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	100	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 ~ +150	
Maximum lead temperature for soldering purposes , 1/8" from case for 5 seconds	T_L	260	

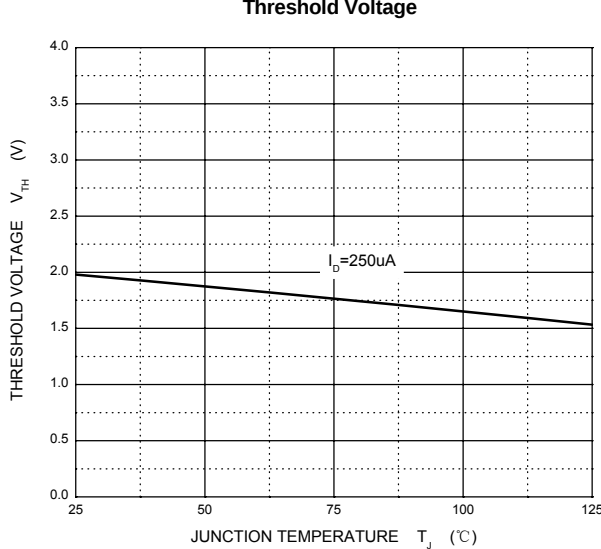
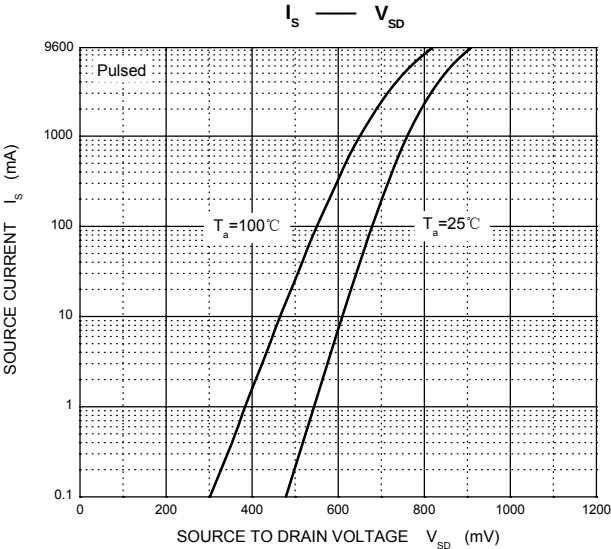
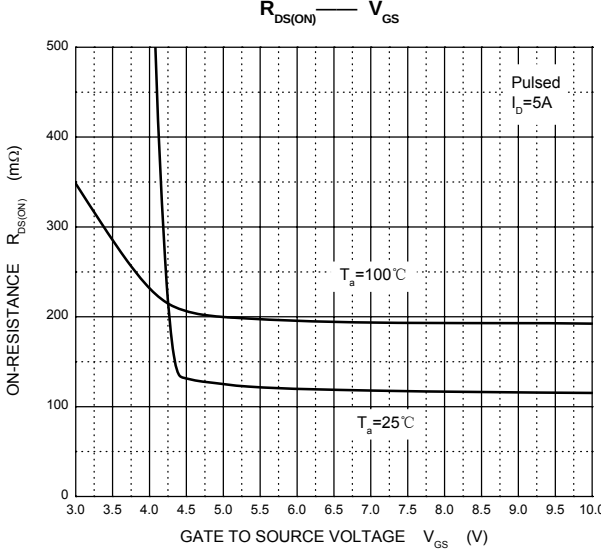
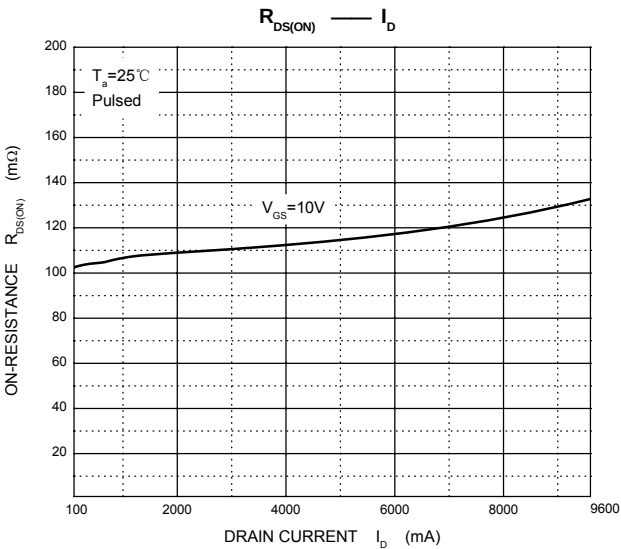
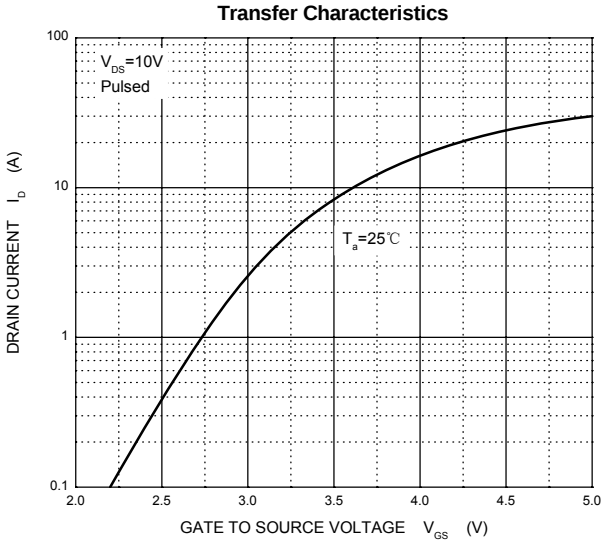
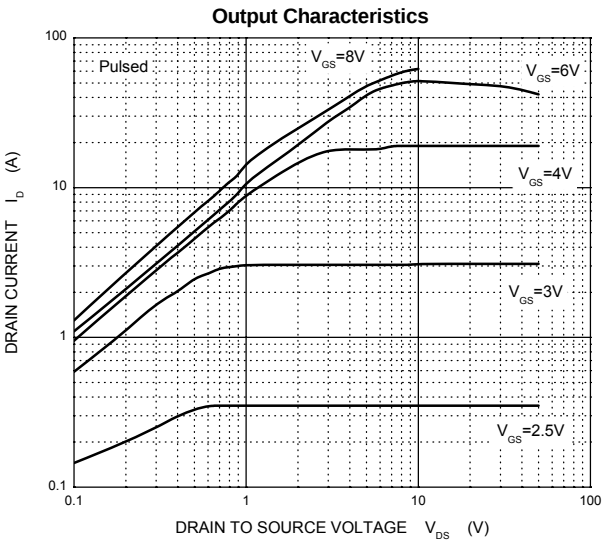
MOSFET ELECTRICAL CHARACTERISTICS

$T_a = 25^\circ\text{C}$ unless otherwise specified

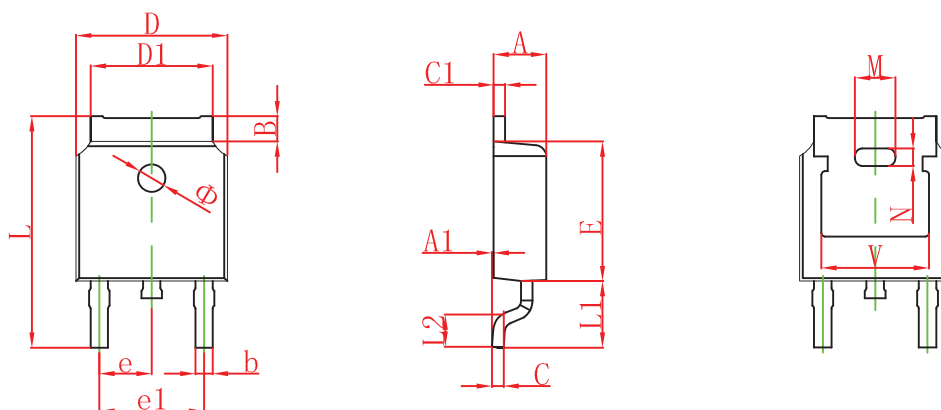
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Off characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	100			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =100V, V _{GS} =0V			1	μA
Gate-body leakage current	I _{GSS}	V _{DS} =0V, V _{GS} =± 20V			± 100	nA
On characteristics (note2)						
Gate-threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.2	2.0	2.5	V
Static drain-source on-resistance	R _{DS(on)}	V _{GS} =10V, I _D =5A		0.115	0.14	Ω
Dynamic characteristics (note 3)						
Input capacitance	C _{iss}	V _{DS} =25V,V _{GS} =0V,f =1MHz		690		pF
Output capacitance	C _{oss}			120		
Reverse transfer capacitance	C _{rss}			90		
Switching characteristics (note 3)						
Turn-on delay time	t _{d(on)}	V _{DD} =30V, R _G =2.5Ω, I _D =2A, V _{GS} =10V		11		ns
Turn-on rise time	t _r			7.4		
Turn-off delay time	t _{d(off)}			35		
Turn-off fall time	t _f			9.1		
Total Gate Charge	Q _g	V _{DS} =30V,V _{GS} =10V,I _D =3A		15.5		nC
Gate-Source Charge	Q _{gs}			3.2		nC
Gate-Drain Charge	Q _{gd}			4.7		nC
Drain-Source Diode Characteristics						
Drain-source diode forward voltage (note2)	V _{SD}	V _{GS} = 0V, I _S =9A			1.2	V
Continuous drain-source diode forward current	I _S				9.6	A
Pulsed drain-source diode forward current	I _{SM}				38.4	A

Notes :

- $I_L = 7A, V_{DD} = 50V, R_G = 25\Omega, \text{Starting } T_J = 25^\circ\text{C}.$
- Pulse Test : Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production

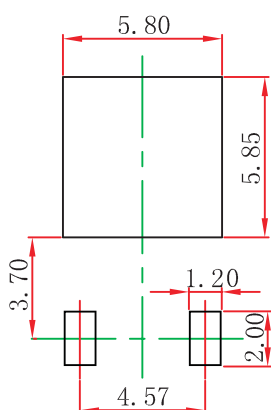


TO-252(4R)-2L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.380	0.087	0.094
A1	0.000	0.100	0.000	0.004
B	0.800	1.400	0.031	0.055
b	0.710	0.810	0.028	0.032
c	0.460	0.560	0.018	0.022
c1	0.460	0.560	0.018	0.022
D	6.500	6.700	0.256	0.264
D1	5.130	5.460	0.202	0.215
E	6.000	6.200	0.236	0.244
e	2.286 TYP.		0.090 TYP.	
e1	4.327	4.727	0.170	0.186
M	1.778REF.		0.070REF.	
N	0.762REF.		0.018REF.	
L	9.800	10.400	0.386	0.409
L1	2.9REF.		0.114REF.	
L2	1.400	1.700	0.055	0.067
V	4.830 REF.		0.190 REF.	
Φ	1.100	1.300	0.043	0.051

TO-252(4R)-2L Suggested Pad Layout



Note:

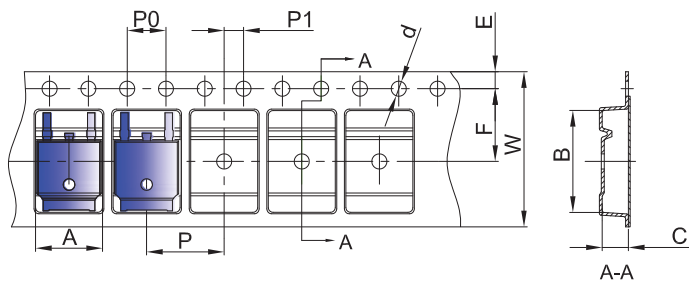
1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.

NOTICE

JCET reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. JCET does not assume any liability arising out of the application or use of any product described herein.

To-252(4R)-2L Tape and Reel

TO-252 Embossed Carrier Tape

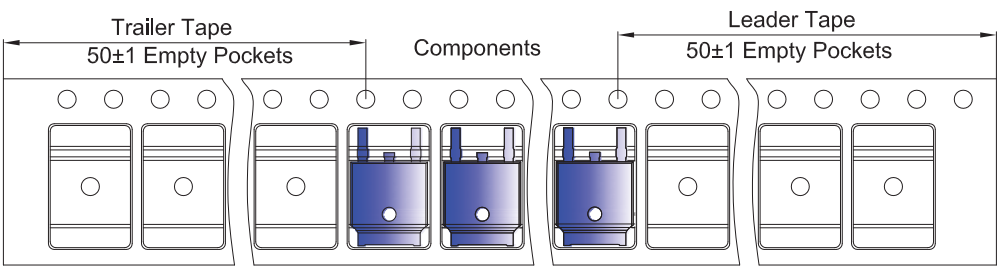


Packaging Description:

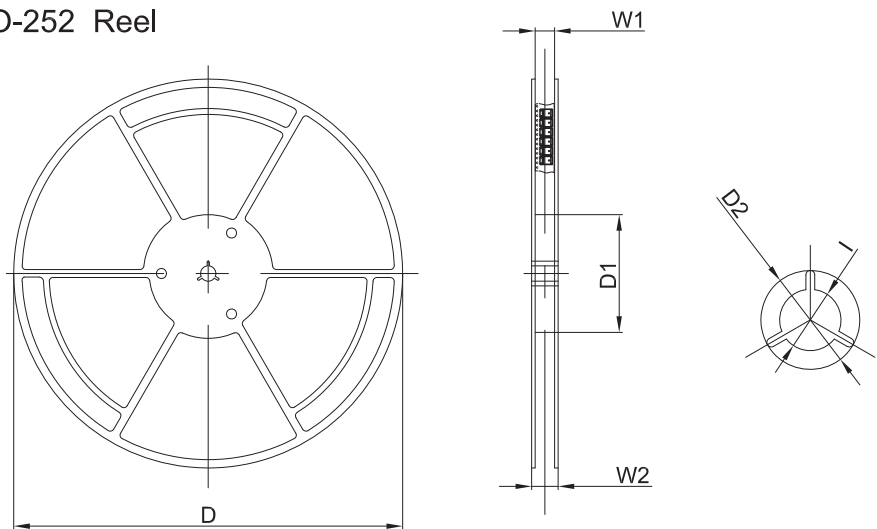
TO-252 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 25,00 units per 13" or 33.0 cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
TO-252	6.90	10.50	2.70	Ø1.55	1.75	7.50	4.00	8.00	2.00	16.00

TO-252 Tape Leader and Trailer



TO-252 Reel



Dimensions are in millimeter						
Reel Option	D	D1	D2	W1	W2	I
13"Dia	330.00	100.00	Ø21.00	16.40	21.00	Ø13.00

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
2,500 pcs	13inch	2,500 pcs	340×336×29	25,000 pcs	353×346×365	